

## ABSTRACT OF DISCLOSURE

5 A semiconductor device including an NMOSFET  
which has an n-type source/drain main region containing  
arsenic and an n-type source/drain buffer region having  
arsenic and phosphorous of which a concentration is  
lower than that of the source/drain main region, and the  
10 concentration of the phosphorous in the source/drain  
buffer region is smaller than the concentration of the  
arsenic therein. The semiconductor device has a  
suppressed reverse short channel effect and reduced p-n  
junction leakage current. Further, the semiconductor  
15 device has a larger margin to a certain gate length and a  
specified threshold voltage to elevate a production yield.